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(54) Title: SILICON COMPOUNDS AND METHODS FOR DEPOSITING FILMS USING SAME

(57) Abstract: A chemical vapor deposition method for producing a dielectric film, the method comprising: providing a substrate into a reaction chamber; introducing gaseous reagents into the reaction chamber wherein the gaseous reagents comprise a silicon precursor comprising a silicon compound having the formula $R_nH_{4-n}Si$ as defined herein and applying energy to the gaseous reagents in the reaction chamber to induce reaction of the gaseous reagents to deposit a film on the substrate. The film as deposited is suitable for its intended use without an optional additional cure step applied to the as-deposited film.

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